

LP5551

PowerWise[™] Technology Compliant Energy Management Unit

General Description

The LP5551 is a PWI 1.0 compliant Energy Management System for reducing power consumption of stand-alone mobile phone processors such as base-band or applications processors.

The LP5551 contains two advanced, digitally controlled switching regulators for supplying variable voltage to processor core and memory. Two regulators provide P- and N- well biasing for threshold scaling applications. The device also integrates 4 programmable LDO-regulators for powering I/O, PLLs and maintaining memory retention in shutdown-mode.

The device is controlled via the PWI open-standard interface. The LP5551 operates cooperatively with PowerWise™ technology compatible processors to optimize supply voltages adaptively over process and temperature variations or dynamically using frequency/voltage pre-characterized look-up tables and provides P- and N-well biasing for threshold scaling.

Features

- 2 300 mA buck regulators operate 180 degrees out of phase for reduced EMI
- 1 MHz PWM switching frequency
- 4 programmable LDOs ideal for I/O (two of these), PLL, and memory retention supply generation.
- Supports high-efficiency PowerWise Technology Adaptive Voltage Scaling
- PWI open standard interface for system power management
- Digitally controlled intelligent voltage scaling
- Auto or PWI controlled PFM mode transition
- Internal soft start/startup sequencing.
- Adjustable P- and N- well bias supply for threshold scaling
- Power OK output.

Applications

- Dual core processors
- GSM/GPRS/EDGE & UMTS cellular handsets
- Hand-held radios
- PDAs
- Battery powered devices
- Portable instruments

System Diagram

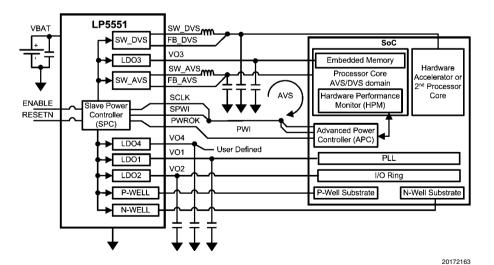


FIGURE 1. System Diagram

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Connection Diagrams and Package Mark Information

36 - Pin LLP

NS Package Number SQA36A

20172102

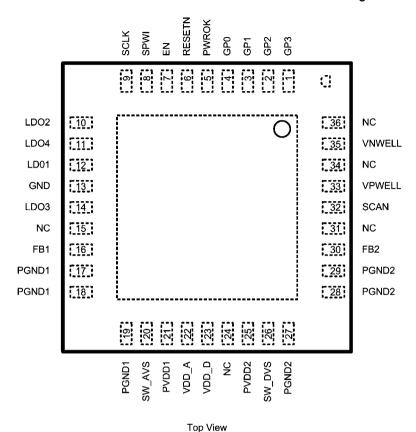
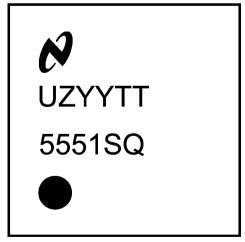


FIGURE 2. LP5551 Pinout

Package Mark



2017214

Note: The actual physical placement of the package marking will vary from part to part.

FIGURE 3. Top View

Typical Application Advanced System Power Controller Connect Die Attach Pad Controller (DAP) to GND DAP 8 6 5 3 SCLK **PWROK** GPO1 GPO3 ΕN SPWI RESETN GPO0 GPO2 1.5 - 3.3V 10 LDO2 NC 36 250 mA O 4.7 μF **1** -0.3 - +1.0V offset 1.5 - 3.3V 250 mA 11 LDO4 VNWELL 35 • (w.r.t. AVS) 10 uA 4.7 μF 2.2V - لم 100 mA NC 34 **12** LD01 -1 - +0.3V offset 13 NC VPWELL 33 (w.r.t. GND) LP5551 10 uA 0.6 - 1.35V 25 mA 14 LDO3 SCAN 32 **LLP-36** 1.0 μF 15 NC NC 31 FB2 30 **16** FB1 PGND2 29 **17** PGND1 PGND2 28 **18** PGND1 SW_AVS VDD_A SW_DVS PVDD1 VDD_D PVDD2 PGND1 PGND2 23 22 μF 22 μF AVS DVS Supply o Supply 0.6V - 1.2V 0.6V - 1.2V 4.7 μΗ $4.7~\mu\text{H}$ 300 mA 300 mA VIN **⋢** 0.1 μF 0.1 μF 22 μF 0.1 μF 2.7V - 5.5 V 20172130

FIGURE 4. Typical Application Circuit

Pin Descriptions

Pin #	Name	I/O	Туре	Description
0	DAP	G	G	Connect Die Attach Pad to ground
1	GP3	0	D	General purpose output pin
2	GP2	0	D	General purpose output pin
3	GP1	0	D	General purpose output pin
4	GP0	0	D	General purpose output pin
5	PWROK	0	D	Power OK, active high output signal

Pin #

Name

RESETN

I/O

Туре

D

Description

Reset, active low

N-well bias voltage

		_		•	_	. 10001, 401.10 1011
_		7	EN	I	D	Enable, active high
		8	SPWI	I/O	D	PowerWise Interface (PWI) bi-directional data
		9	SCLK	I	D	PowerWise Interface (PWI) clock input
		10	LDO2	Р	Р	LDO2 output, for supplying the I/O voltage on the SoC
		11	LDO4	Р	Р	LDO4 output, for supplying a fixed voltage to a PLL etc. on the SoC
		12	LDO1	Р	Р	LDO1 output, user defined
		13	NC			
		14	LDO3	Р	Р	LDO3 output, on-chip memory supply voltage
		15	NC			
		16	FB1	Р	Р	AVS switcher feedback
		17	PGND1	G	G	Power ground for the AVS switcher
www.DataSheet	ll I c	18	PGND1	G	G	Power ground for the AVS switcher
www.bataoneer	.0.0	19	PGND1	G	G	Power ground for the AVS switcher
		20	SW1	Р	Р	AVS Switcher switch node; connected to inductor
		21	PVDD1	Р	Р	Battery supply voltage for the AVS switcher
		22	VDD_D	Р	Р	Battery supply voltage for digital
		23	VDD_A	Р	Р	Battery supply voltage for analog
		24	NC			
		25	PVDD2	Р	Р	Battery supply voltage for the DVS switcher
		26	SW2	Р	Р	DVS Switcher switch node; connected to inductor
		27	PGND2	G	G	Power ground for the DVS switcher
		28	PGND2	G	G	Power ground for the DVS switcher
		29	PGND2	G	G	Power ground for the DVS switcher
		30	FB2	Р	Р	DVS switcher feedback
		31	NC			
		32	SCAN			
		33	VPWELL	Р	Р	P-well bias voltage
		34	NC			

A: Analog Pin

35

36

VNWELL

NC

D: Digital Pin

I: Input Pin

O: Output Pin

I/O: Input/Output Pin

P: Power Pin

G: Ground Pin

Ordering Information

Voltage Option	Order Number	Package Marking	Supplied As
	LP5551SQ	LP5551SQ	1000 units, Tape-and-Reel
	LP5551SQX	LP5551SQ	4500 units, Tape-and-Reel

 $^{^*}$ Released. Samples available.

(Note 4)

Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

VDD_A, VDD_D, PVDD1, and

-0.3 to +6.0V

PVDD2

LDO1, LDO2, LDO3, LDO4, -0.3 to VDD_A + 0.3V

VNWELL to GND, VPwell, ENABLE, RESETN, FB1, FB2, SW_AVS, SW_DVS,GP0, GP1, GP2, and GP3

-0.3 to VDD_D + 0.3V SPWI, SCLK, PWROK GND, PGND1, PGND2, to GND ±0.3V

SLUG

Junction Temperature (TJ-MAX) Storage Temperature Range

150°C -65°C to 150°C

Maximum Continuous Power Dissipation (PD-MAX) (Note 5) TBD W

Maximum Lead Temperature

(Soldering) ESD Rating (Note 3)

Human Body Model:

All pins

2.0kV

Operating Ratings (Notes 1, 2)

VDD_A, VDD_D, PVDD1, and PVDD2 2.7 V to 5.5 V Junction Temperature (T_I) Range -40°C to +125°C Ambient Temperature (T_△) Range(Note -40°C to +85°C

Thermal Properties (Note 6)

Junction-to-Ambient Thermal 39.8°C/W

Resistance (θ_{IA})

3.6V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8, 9)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
I _Q	Shutdown Supply current	$V_{DD_A,_D}$, $P_{VDD1,2} = 3.6 \text{ V}$, all circuits off.		0.44	4	μА
		$-40^{\circ}\text{C} \leq \text{TJ} \leq 125^{\circ}\text{C}$ $V_{\text{DD_A, _D}}, P_{\text{VDD1,2}} = 3.6 \text{ V, all circuits}$ off. $-40^{\circ}\text{C} \leq \text{TJ} \leq 85^{\circ}\text{C}$		1	12	μΑ
	Sleep State Supply Current	V _{DD_A, _D} , V _{PVDD1,2} = 3.6 V, LDO3 on, LDO2 on (no load). All other circuits off.		135	186	μΑ
	Acitve State Supply Current	V _{DD_A, _D} , V _{PVDD1,2} = 3.6 V, all outputs on, no load		431	742	μΑ
UVLO high	Under Voltage Lockout, high threshold				2.7	
UVLO low	Under Voltage Lockout, low threshold		2.5			
T _{SD}	Thermal Shutdown Threshold			160		°C
	Thermal Shutdown Hysteresis			10		

LDO1 (PLL/Fixed Voltage) Characteristics Unless otherwise noted, V_{DD A. D}, V_{PVDD1.2} RESETN, ENABLE = 3.6V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{OUT}	Output Voltage	I _{OUT} = 50 mA,	-3.5%	1.2	3.1%	V
Accuracy		V _{OUT} = 1.2 V,				
		$2.7 \text{ V} \le \text{V}_{DD A. D}, \text{V}_{PVDD1.2} \le 5.5 \text{ V}$				
V _{OUT} Range	Programmable Output Voltage	Programming Resolution=100 mV	0.7	1.2	2.2	V
	Range					
I _{OUT}	Rated Output Current	2.7 V ≤ V _{DD_A, _D} ,P _{VDD1,2} ≤ 5.5 V	0		100	mA
	Output Current Limit	V _{OUT} = 0 V			347	
I _Q	Quiescent Current	I _{OUT} = 0 mA(Note 11)		35		μΑ

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Symbol **Parameter** Conditions Min Тур Max Units Line Regulation ΔV_{OUT} -0.083 0.316 %/V $2.7 \text{ V} \le \text{V}_{\text{DD_A, }_{-}\text{D}}, \text{V}_{\text{PVDD1,2}} \le 5.5 \text{ V},$ $I_{OUT} = 50 \text{ mA}$ Load Regulation -0.013 0.013 %/mA $V_{DD_A, D}, V_{PVDD1,2} = 3.6 \text{ V}, 1 \text{ mA} \le$ I_{OUT} ≤ 100 mA $3.6 \text{ V} \le \text{V}_{\text{DD}_A, _D}, \text{V}_{\text{PVDD1},2} \le 3.9 \text{ V},$ Line Transient Regulation 27 mV TRISE,FALL = 10 µs Load Transient Regulation $V_{DD A, D}, V_{PVDD1,2} = 3.6 V,$ mV 86 10 mA \leq I_{OUT} \leq 90 mA, $T_{RISE,FALL} = 100 \text{ ns}$ eΝ Output Noise Voltage 10 Hz ≤ f ≤ 100 kHz, 0.103 mVRM S $C_{OUT} = 2.2 \mu F$ PSRR Power Supply Ripple Rejection f = 1 kHz,dΒ 56 Ratio $C_{OUT} = 2.2 \mu F$ f = 10 kHz,dB 36 $C_{OUT} = 2.2 \mu F$ C_{OUT} **Output Capacitance** 2.2 20 μF $0 \text{ mA} \le I_{OUT} \le 100 \text{ mA}$ **Output Capacitor ESR** 500 $\mathsf{m}\Omega$ Start-Up Time from Shut-down $C_{OUT} = 1 \mu F$, 54 μs t_{START-UP}

LDO2 (I/O Voltage) Characteristics Unless otherwise noted, $V_{DD_A,_D}$, $V_{PVDD1,2}$ RESETN, ENABLE = 3.6 V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8)

 $I_{OUT} = 100 \text{ mA}$

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{OUT} Accuracy	Output Voltage	I _{OUT} = 125 mA,	-3.7%	3.3	2.8%	V
		V _{OUT} = 3.3 V,				
		$3.6 \text{ V} \le \text{V}_{\text{DD A. D}} \le 5.5 \text{ V}$				
V _{OUT} Range	Programmable Output Voltage	1.5-2.3 V =100 mV step, 2.5 V, 2.8 V,	1.5	3.3	3.3	V
	Range	3.0 V and 3.3 V				
I _{OUT}	Rated Output Current	$3.6 \text{ V} \le \text{V}_{\text{DD_A}, _D}, \text{V}_{\text{PVDD1},2} \le 5.5 \text{ V}$	0		250	mA
	Output Current Limit	V _{OUT} = 0V			615	
	Dropout Voltage(Note 10)	I _{OUT} = 125 mA		65	192	mV
I _Q	Quiescent Current	I _{OUT} = 0 mA (Note 11)		55		μA
ΔV_{OUT}	Line Regulation	$3.6 \text{ V} \le \text{V}_{\text{DD A, D}} \le 5.5 \text{ V},$	-0.08		0.312	%/V
		I _{OUT} = 125 mA				
	Load Regulation	$V_{DD_A, D}, V_{PVDD1,2} = 3.6 \text{ V}, 1 \text{ mA} \le$	-0.018		0.018	%/mA
		I _{OUT} ≤ 250 mA				
	Line Transient Regulation	$3.6 \text{ V} \le \text{V}_{\text{DD A. D}}, \text{V}_{\text{PVDD1.2}} \le 3.9 \text{ V},$		24		mV
		$T_{RISE,FALL} = 10 \text{ us}$				
	Load Transient Regulation	V _{DD A, D} , V _{PVDD1,2} = 3.6 V,		246		mV
		25 mA ≤ I _{OUT} ≤ 225 mA,				
		T _{RISE,FALL} = 100 ns				
eN	Output Noise Voltage	10 Hz ≤ f ≤ 100 kHz,		0.120		mVRM
		C _{OUT} = 4.7 μF				S
PSRR	Power Supply Ripple Rejection			46		dB
	Ratio	C _{OUT} = 4.7 μF				
		f = 10 kHz,		34		
		C _{OUT} = 4.7 μF				

Symbol	Parameter	Conditions	Min	Тур	Max	Units
C _{OUT}	Output Capacitance	0 mA ≤ I _{OUT} ≤ 250 mA	2	4.7	20	μF
	Output Capacitor ESR		5		500	mΩ
t _{START-UP}	Start-Up Time from Shut-down	C _{OUT} = 4.7 μF, I _{OUT} = 250 mA		144		μs

LDO3 (Memory Retention Voltage) Characteristics Unless otherwise noted, $V_{DD_A,_D}$, $V_{PVDD1,2}$ RESETN, ENABLE = 3.6V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{OFFSET}	Active State Buffer offset (=	25 mA≤I _{OUT} ≤ 50 mA,	0	12	82	mV
	V _{O3} -V _{FB}) Output	V _{DD_A, _D} , V _{PVDD1,2} = 3.6V,				
		AVS switcher V _{OUT} = 1.2 V,				
		200 mA ≤ AVS switcher I _{OUT} ≤ 300 mA				
SIQUTt4U.com	Sleep state: Memory retention	$I_{OUT} = 5 \text{ mA}, V_{OUT} = 1.2 \text{ V},$	-3.6%	1.2	3.6%	V
Accuracy	voltage regulation	$2.7 \text{ V} \le \text{V}_{DD A. D}, \text{V}_{PVDD1.2} \le 5.5 \text{ V}$				
V _{OUT} Range	Programmable Output Voltage	Programming Resolution=50 mV	0.6	1.2	1.35	V
	Range					
	(Sleep state)					
I _o	Quiescent Current	Active mode,		33	44	μΑ
		I _{OUT} = 10 μA (Note 11)				
		Sleep mode,		10	16	μΑ
		I _{OUT} = 10 μA (Note 11)				
I _{OUT}	Rated Output Current, Active state	$2.7 \text{ V} \le \text{V}_{\text{DD_A, }_{-}\text{D}}, \text{V}_{\text{PVDD1,2}} \le 5.5 \text{ V}$			50	mA
	Rated Output Current, Sleep state	$2.7 \text{ V} \le \text{V}_{\text{DD_A, }_{-}\text{D}}, \text{V}_{\text{PVDD1,2}} \le 5.5 \text{ V}$			5	
	Output Current Limit, Active state	V _{OUT} = 0 V			397	
eN	Output Voltage Noise	10 Hz ≤ f ≤ 100 kHz,		0.0158		mVRMS
		C _{OUT} = 1μF				
PSRR	Power Supply Ripple Rejection Ratio			36		dB
C _{OUT}	Output Capacitance	0 mA ≤ I _{OUT} ≤ 5 mA	0.7	1	2.2	μF
	Output Capacitor ESR		5		500	mΩ

LDO4 Characteristics Unless otherwise noted, $V_{DD_A,_D}$, $V_{PVDD1,2}$ RESETN, ENABLE = 3.6V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{OUT} Accuracy	Output Voltage	I _{OUT} = 125 mA,	-3.7%	3.3	3.1%	V
		V _{OUT} = 3.3 V,				
		$3.6 \text{ V} \le \text{V}_{DD A. D}, \text{V}_{PVDD1,2} \le 5.5 \text{ V}$				
V _{OUT} Range	Programmable Output Voltage	1.5-2.3 V =100 mV step, 2.5 V, 2.8V,	1.5	3.3	3.3	V
	Range	3.0 V and 3.3 V				
I _{OUT}	Rated Output Current	$3.6 \text{ V} \le \text{V}_{\text{DD_A}, _D}, \text{V}_{\text{PVDD1},2} \le 5.5 \text{ V}$	0		250	mA
	Output Current Limit	V _{OUT} = 0 V			629	
	Dropout Voltage(Note 10)	I _{OUT} = 125 mA		65	246	mV
I _Q	Quiescent Current	I _{OUT} = 0 mA (Note 11)		55		μΑ

555	Symbol	Parameter	Conditions	Min	Тур	Max	Units
LP.	ΔV_{OUT}	Line Regulation	$3.6 \text{ V} \le \text{V}_{\text{DD_A, _D}}, \text{V}_{\text{PVDD1,2}} \le 5.5 \text{ V},$	-0.081		0.306	%/V
			I _{OUT} = 125 mA				
		Load Regulation	$V_{IN} = 3.6 \text{ V}, 1 \text{ mA} \le I_{OUT} \le 250 \text{ mA}$	-0.018		0.018	%/mA
		Line Transient Regulation	$3.6 \text{ V} \le \text{V}_{\text{DD_A, _D}}, \text{V}_{\text{PVDD1,2}} \le 3.9 \text{ V},$		24		mV
			T _{RISE,FALL} = 10 us				
		Load Transient Regulation	$V_{DD_A, D}, V_{PVDD1,2} = 3.6 V,$		246		mV
			25 mA ≤ I _{OUT} ≤ 225 mA,				
			T _{RISE,FALL} = 100 ns				
	eN	Output Noise Voltage	10 Hz ≤ f ≤ 100 kHz,		0.120		mVRM
			C _{OUT} = 4.7 μF				S
	PSRR	Power Supply Ripple Rejection	f = 1 kHz,		46		dB
		Ratio	C _{OUT} = 4.7 μF				
www.DataSheet4U	J.com		f = 10 kHz,		34		
			C _{OUT} = 4.7 μF				
	C _{OUT}	Output Capacitance	0 mA ≤ I _{OUT} ≤ 250 mA	2	4.7	20	μF
		Output Capacitor ESR		5		500	mΩ
1	t _{START-UP}	Start-Up Time from Shut-down	C _{OUT} = 4.7 μF, I _{OUT} = 250 mA		144		μs

AVS/DVS Switcher Characteristics Unless otherwise noted, $V_{DD_A,_D}$, $V_{PVDD1,2}$, RESETN, ENABLE = 3.6V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{OUT} Accuracy	Output Voltage	I _{OUT} = 200 mA, V _{OUT} = 1.2 V,	-4.1%	1.2	4.3%	V
		$V_{DD A. D}, V_{PVDD1.2} = 3.6 V$				
V _{OUT} Range	Programmable Output Voltage	Programming Resolution = 4.7 mV	0.6	1.2	1.2	V
	Range					
ΔV_{OUT}	Line regulation	2.7V < V _{DD_A, _D} , V _{PVDD1,2} <5.5 V,		0.18		%/V
		I _{OUT} = 10 mA				
	Load regulation	$V_{DD_A, D}, V_{PVDD1,2} = 3.6 \text{ V}$		0.011		%/mA
		I _{OUT} = 100-300 mA				
IQ	Quiescent current consumption	I _{OUT} = 0 mA		15		μΑ
R _{DSON(P)}	P-FET resistance	$V_{DD_A, D}, V_{PVDD1,2} = VGS = 3.6 V$		425	690	mΩ
R _{DSON(N)}	N-FET resistance	$V_{DD_A, D}, V_{PVDD1,2} = VGS = 3.6 V$		345	635	mΩ
I _{LIM}	Switch peak current limit	2.7 V < V _{DD_A, _D} <5.5 V	350	520	750	mA
f _{OSC}	Internal oscillator frequency	PWM-mode	805	1000	1125	kHz
C _{OUT}	Output Capacitance	0 mA ≤ I _{OUT} ≤ 300 mA		22		μF
	Output Capacitor ESR		5		500	mΩ
L	Inductor inductance	0 mA ≤ I _{OUT} ≤ 300 mA		4.7		μН
R _{VFB}	V _{FB} pin resistance to ground		150		440	kΩ

N-Well Bias Characteristics Unless otherwise noted, $V_{DD_A,_D}$, $V_{PVDD1,2}$, RESETN, ENABLE = 3.6V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{OFFSET} Accuracy	Output Voltage Offset Tolerance	$V_{AVS} = 1.2 \text{ V}$ $V_{OFFSET} = -0.3 \text{ V}$ $Iout = 10 \mu A$	-0.363	-0.3	-0.266	V
	Line Regulation	$2.7 \le V_{DD_A,_D}, P_{VDD1,2} \le 5.5 \text{ V}$ $I_{OUT} = 10 \text{ uA}, V_{OFFSET} = -0.315$ $2.7 \text{ V} \le V_{DD_A,_D}, P_{VDD1,2} \le 5.5 \text{ V}$		0.321		%/V
	Load Regulation	$V_{DD_A,_D}, P_{VDD1,2} = 3.6 \text{ V}$ $VAVS = 1.2 \text{ V}$ $0.1 \text{ uA} \leq IOUT \leq 10 \text{ uA}$		-0.107		%/mA
V _{OFFSET}	Programmable Output Voltage Offset: Referenced to V _{AVS}	Programming Resolution: See Register Table	-0.315	0	1	V
lα	Quiescent Current			50		uA
I _{SOURCE/SINK}	Output Sourcing and Sinking Capability	$V_{DD_A,_D}$, $P_{VDD1,2} = 3.6 \text{ V}$, $V_{OFFSET} = 1 \text{ V}$ $V_{OFFSET} > V_{OFFSET(NOM)} - 15 \text{ mV}$ Steady State	3			mA
I _{SC (SOURCE)}	Output Source Short Circuit Limit	V _{DD_A, _D} , P _{VDD1,2} = 3.6 V, V _{NWELL} = 0 V Steady State			42	mA
I _{SC (SINK)}	Output Sink Short Circuit Limit	$V_{DD_A,_D}$, $P_{VDD1,2} = 3.6 \text{ V}$, $V_{NWELL} = V_{DD_A}$ Steady State			65	mA
C _{LOAD}	Output Capacitance Of Load	0 μA ≤I _{OUT} ≤ 3 uA	0.1	1	5	nF

P-Well Characteristics Unless otherwise noted, $V_{DD_A,_D}$, $V_{PVDD1,2}$, RESETN, ENABLE = 3.6V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{OUT} Accuracy	Output Voltage Tolerance	$V_{OUT} = 0 V$ $I_{OUT} = 10 \mu A$	-0.035	0	0.035	V
		$2.7 \le V_{DD_A,_D}$, $P_{VDD1,2} \le 5.5 \text{ V}$ Bias Current Control bits = 00				
	Line Regulation	$I_{OUT} = 10 \text{ uA}$ $V_{OUT} = 0.3 \text{ V}$ $2.7\text{V} \le V_{DD_A,_D}, P_{VDD1,2} \le 5.5 \text{ V}$		0.159		%/V
	Load Regulation	$V_{DD_A,_D}$, $P_{VDD1,2} = 3.6 \text{ V}$ $V_{OUT} = 0.3 \text{ V}$ $0.1 \text{ uA} \le I_{OUT} \le 10 \text{ uA}$		0.011		%/µA
V _{OUT} Range	Programmable Output Voltage Offset: Referenced to Ground	0 mA ≤ I _{OUT} ≤ 10 uA Programming Resolution: See Register Table	-1	0	0.3	V
IQ	Quiescent Current	IOUT = 0, P-well Bias Current Control bits = 00		150	270	uA

Symbol	Parameter	Conditions	Min	Тур	Max	Units
I _{SINK}	Output Sinking Capability	V _{DD_A, _D} , P _{VDD1,2} = 3.6 V Bias Current Control bits = 00	8			uA
		V _{OUT} > V _{OUT(NOM)} - 15 mV(Note 12)				
		V _{DD_A, _D} , P _{VDD1,2} = 3.6 V Bias Current Control bits = 01	36			
		$V_{OUT} > V_{OUT(NOM)} - 15 \text{ mV(Note 12)}$				
		V _{DD_A, _D} , P _{VDD1,2} = 3.6 V Bias Current Control bits = 10	52			
		$V_{OUT} > V_{OUT(NOM)} - 15 \text{ mV(Note 12)}$				
		$V_{DD_A,_D}$, $P_{VDD1,2} = 3.6 \text{ V}$ Bias Current Control bits = 11 $V_{OUT} > V_{OUT(NOM)}$ - 15 mV(Note 12)	80			
I _{SOURCE}	Output Source Capability	V _{DD_A, _D} , P _{VDD1,2} = 2.7 V	100			uA
C _{LOAD}	Output Capacitance of Load	0μA ≤ I _{OUT} ≤ 3 uA	0.1	1	5	nF

Logic and Control Inputs Unless otherwise noted, $V_{DD_A,_D}$, $V_{PVDD1,2}$, RESETN, ENABLE = 3.6V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8, 9)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
PWI _{CLOCK}	Rated frequency	$2.7 \text{ V} \le \text{V}_{\text{DD_A, }_\text{D}}, \text{V}_{\text{PVDD1,2}} \le 5.5 \text{ V}$			15	MHz
V _{IL}	Input Low Level	ENABLE, RESETN, SPWI, SCLK 2.7			0.4	V
		$V \le V_{DD_A, D}, V_{PVDD1,2} \le 5.5 V$				
V_{IH}	Input High Level	ENABLE, RESETN 2.7 V \leq V _{DD_A, _D} ,	2			V
		$V_{PVDD1,2} \le 5.5 \text{ V}$				
V_{IH_PWI}	Input High Level, PWI	SPWI, SCLK, 1.5 V ≤V _{O2} ≤ 3.3 V	V ₀₂ -0.4V			V
I _{IL}	Logic Input Current	ENABLE, RESETN, 0 V ≤ V _{DD A, D} ,	-5		5	μА
		V _{PVDD1,2} ≤ 5.5 V				
I _{IL_PWI}	Logic Input Current, PWI	SPWI, SCLK, 1.5 V ≤ V _{O2} ≤ 3.3 V	-5		15	μΑ
R _{PD_PWI}	Pull-down resistance for PWI signals		0.5	1	2	МΩ
T _{EN_LOW}	Minimum low pulse width to enter STARTUP state	ENABLE pulsed high - low - high		10		µsec

Logic and Control Outputs Unless otherwise noted, $V_{DD_A,_D}$, $V_{PVDD1,2}$, RESETN, ENABLE = 3.6V. Typical values and limits appearing in normal type apply for TJ = 25°C. Limits appearing in boldface type apply over the entire junction temperature range for operation, -40 to +125°C. (Notes 2, 7, 8, 9)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{OL}	Output low level	PWROK, GPOx, SPWI,			0.4	٧
		I _{SINK} ≤ 1 mA				
V _{OH}	Output high level	PWROK, GPOx, I _{SOURCE} ≤ 1 mA	V _{BAT1} -0.4V			٧
V _{OH_PWI}	Output high level, PWI	SPWI, I _{SOURCE} ≤ 1 mA	V _{O2} -0.4V			V

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the component may occur. Operating Ratings are conditions under which operation of the device is guaranteed. Operating Ratings do not imply guaranteed performance limits. For guaranteed performance limits and associated test conditions, see the Electrical Characteristics tables.

Note 2: All voltages are with respect to the potential at the GND pin.

Note 3: The Human body model is a 100 pF capacitor discharged through a 1.5 k Ω resistor into each pin.

The amount of Absolute Maximum power dissipation allowed for the device depends on the ambient temperature and can be calculated using the formula $P = (TJ - TA)/\theta_{JA}$, (1) where TJ is the junction temperature, TA is the ambient temperature, and JA is the junction-to-ambient thermal resistance.

Junction-to-ambient thermal resistance is highly application and board-layout dependent. In applications where high maximum power dissipation exists, special care must be paid to thermal dissipation issues in board design.

Internal thermal shutdown circuitry protects the device from permanent damage. Thermal shutdown engages at TJ=150°C (typ.) and disengages at TJ=140°C (typ.).

Note 4: For detailed soldering specifications and information, please refer to National Semiconductor Application Note 1187: Leadless Leadframe Package (LLP) (AN-1187).

Note 5: In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be derated. Maximum ambient temperature (TA-MAX) is dependent on the maximum operating junction temperature (TJ-MAX-OP = 125°C), the maximum power dissipation of the device in the application (PD-MAX), and the junction-to ambient thermal resistance of the part/package in the application (θ_{JA}), as given by the following equation: TA-MAX = TJ-MAX-OP - (θ_{JA} × PD-MAX).

Note 6: Junction-to-ambient thermal resistance (θJA) is taken from a thermal modeling result, performed under the conditions and guidelines set forth in the JEDEC standard JESD51-7. The test board is a 4-layer FR-4 board measuring 102mm x 76mm x 1.6mm with a 2x1 array of thermal vias. The ground plane on the board is 50mm x 50mm. Thickness of copper layers are 36μm/18μm/36μm (1.5oz/1oz/1.5oz). Ambient temperature in simulation is 22°C, still air. Power dissipation is 1W.

Junction-to-ambient thermal resistance is highly application and board-layout dependent. In applications where high maximum power dissipation exists, special care must be paid to thermal dissipation issues in board design.

The value of θ_{JA} of this product can vary significantly, depending on PCB material, layout, and environmental conditions. In applications where high maximum power dissipation exists (high VIN, high IOUT), special care must be paid to thermal dissipation issues. For more information on these topics, please refer to Application Note 1187: Leadless Leadframe Package (LLP) and the Power Efficiency and Power Dissipation section of this datasheet.

Note 7: All limits are guaranteed by design, test and/or statistical analysis. All electrical characteristics having room-temperature limits are tested during production with TJ = 25C. All hot and cold limits are guaranteed by correlating the electrical characteristics to process and temperature variations and applying statistical process control

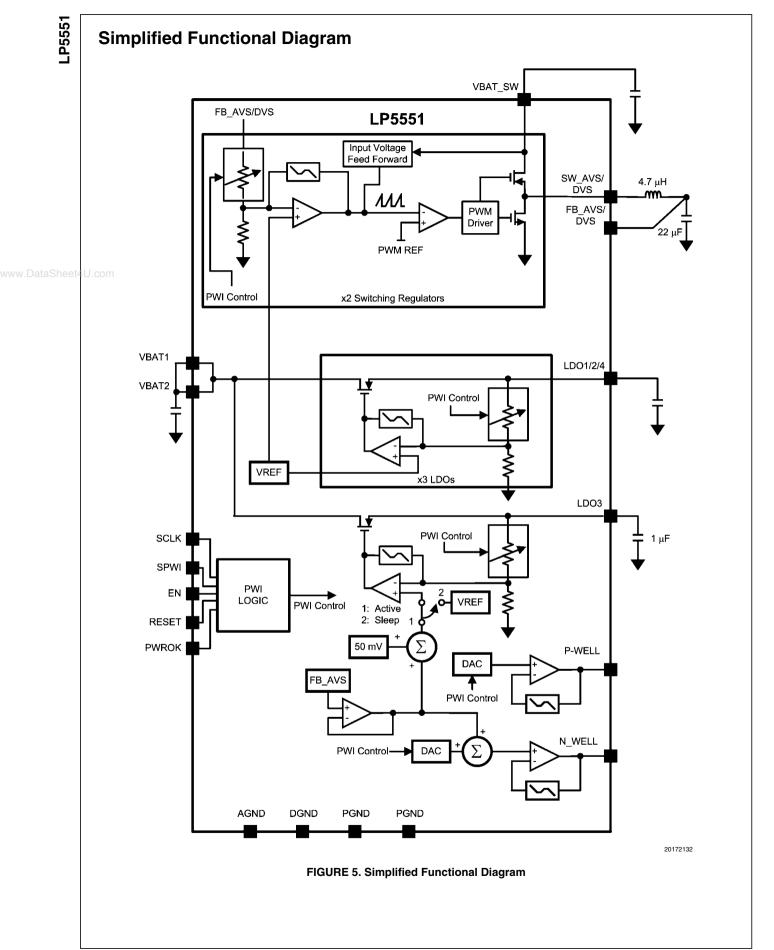
Note 8: Capacitors: Low-ESR Surface-Mount Ceramic Capacitors are (MLCCs) used in setting electrical characteristics

Note 9: Guaranteed by design.

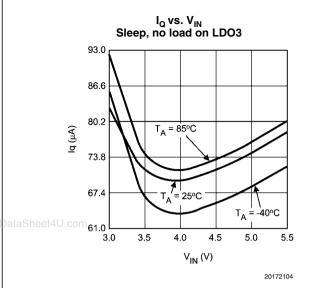
Note 10: Dropout voltage is the input-to-output voltage difference at which the output voltage is 100mV below its nominal value. This specification does not apply in cases it implies operation with an input voltage below the 2.7V minimum appearing under Operating Ratings. For example, this specification does not apply for devices having 1.5V outputs because the specification would imply operation with an input voltage at or about 1.5V

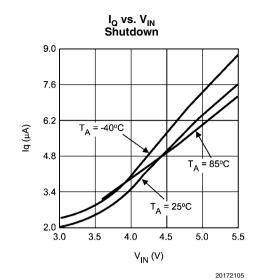
Note 11: Quiescent current for LDO1, LDO2, LDO3, and LDO4 do not include shared functional blocks such as the bandgap reference.

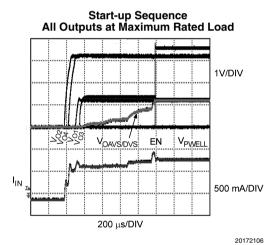
Note 12: The output voltage is guaranteed not to drop more than 15 mV (V_{OUT} < V_{OUT(NOM)} - 15 mV) while sinking the specified current.

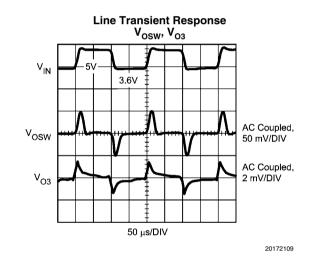


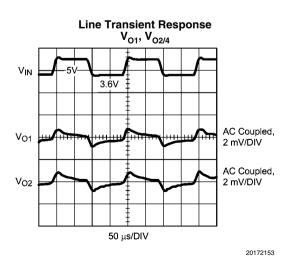
Typical Performance Characteristics Unless otherwise stated: V_{IN}=3.6V

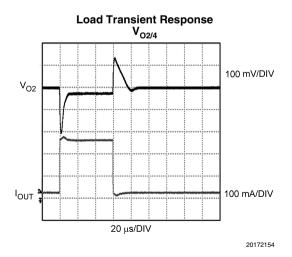


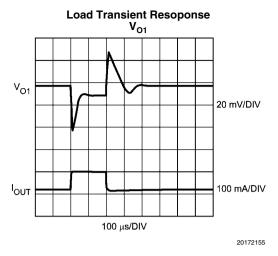


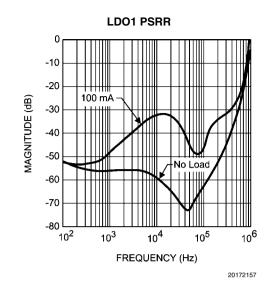




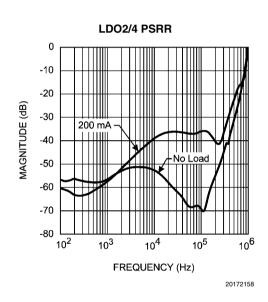


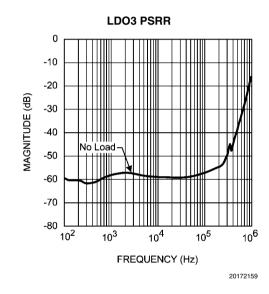






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Switching Frequency vs. V_{IN}

1.10M

T_A = 85°C

T_A = 85°C

T_A = 25°C

T_A = -40°C

970.00k

3.0

3.5

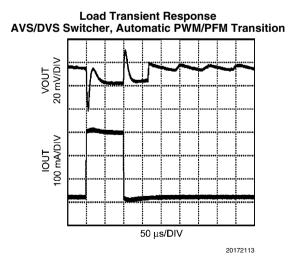
4.0

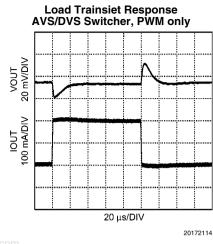
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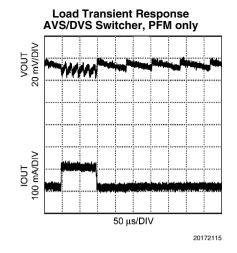
5.0

5.5

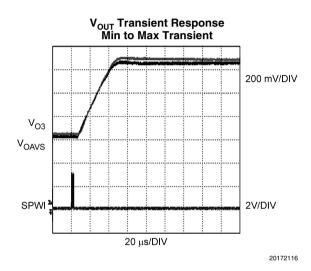
V_{IN} (V)

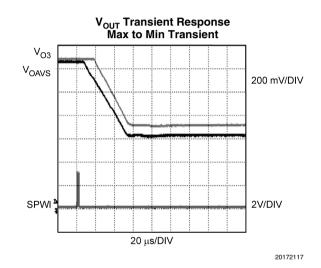




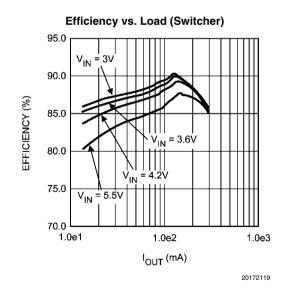


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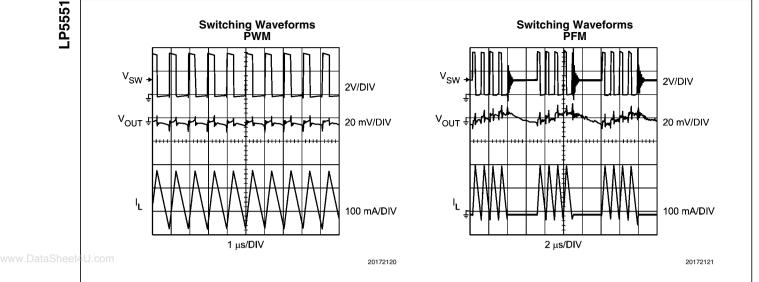




Switch Current Limit vs. V_{IN} 570.0 = 85°C $T_A = 25^{\circ}C$ 554.0 (YE) 538.0 - 522.0 538.0 = -40°C 506.0 490.0 - 3.0 3.5 4.0 4.5 5.0 5.5 $V_{|N|}(V)$ 20172118







LP5551 PWI Register Map

The PWI standard supports sixteen 8-bit registers on the PWI slave. The table below summarizes these registers and shows default register bit values after reset. The following sub-sections provide additional detail on the use of each individual register.

Summary

Register	Register	Register Usage	Туре	Res	Reset Default Value						
Address	Name			7	6	5	4	3	2	1	0
0x0	R0	Core voltage	R/W	0	1	1	1	1	1	1	1
0x1	R1	Unused	R/W	-	-	-	-	-	-	-]-
0x2	R2	Memory retention voltage	R/W	0	1	1	0	0	-	-	-
0x3	R3	Status register	R/O	0	0	0	0	1	1	1	1
0x4	R4	PWI version number	R/O	0	0	0	0	0	0	0	1
0x5	R5	N-well Bias	R/W	0	0	0	0	0	0	-	-
0x6	R6	P-well Bias	R/W	0	0	0	0	0	0	-	-
0x7	R7	LDO2 voltage	R/W	0	1	1	1	1	-	-	-
0x8	R8	LDO1 voltage	R/W	0	0	1	0	1	-	-	-
0x9	R9	PFM/PWM force	R/W	0	0	-	Ī-	-	-	-	-
0xA	R10	SW_DVS voltage	R/W	-	-	-	-	-	-	-	-
0xB	R11	Enable Control	R/W	-	-	1	1	1	1	1	1
0xC	R12	LDO 4 voltage	R/W	0	1	1	1	1	-	-]-
0xD	R13	GPO Control	R/W	0	0	0	0	0	0	0	0
0xE	R14	Reserved	R/W	-	-	-	-	-	-	-	-
0xF	R15	Reserved	R/W	-	-	-	Ī-	-	-	-	Ī-

R0 - Core Voltage Register

Address 0x0

Type R/W

Bit	Field Name	Description or Comment	Description or Comment		
7	Sign		This bit is fixed to '0'. Reading this bit will result in a '0'. Any data written into this bit position using the Register Write command is ignored.		
6:0	Voltage	Core voltage value. Default value	e is in bold .		
		Voltage Data Code [7:0]	Voltage Value (V)		
		7h'00	0.6		
		7h'xx	Linear scaling		
		7h'7f	1.2 (default)		

R1 - Unused Register

Address 0x1

Type R/W

Reset Default 8h'00

Bit	Field Name	Description or Comment	
7:0	Unused	Write transactions to this register are ignored. Read transactions will	
		return a "No Response Frame." A no response frame contains all zeros	
		(see PWI 1.0 specification).	

R2 – VO3 Voltage Register (Memory Retention Voltage)

Address 0x2

Type R/W

Bit	Field Name	Description or Comment	Description or Comment				
7	Sign	This bit is fixed to '0'. Reading this bit will	result in a '0'. Any data written into this bit				
		position using the Register Write comma	position using the Register Write command is ignored.				
6:3	Voltage	Fixed voltage value. A code of all ones in	dicates maximum voltage while a code of				
		all zero indicates minimum voltage. Defa	ult value is in bold .				
		Voltage Data Code [6:3]	Voltage Value (volts)				
		4h'0	0.6				
		4h'1	0.65				
		4h'2	0.7				
		4h'3	0.75				
		4h'4	0.8				
		4h'5	0.85				
		4h'6	0.9				
		4h'7	0.95				
		4h'8	1				
		4h'9	1.05				
		4h'A	1.1				
		4h'B	1.15				
		4h'C	1.20 (default)				
		4h'D	1.25				
		4h'E	1.3				
		4h'F	1.35				
2:0	Unused	These bits are fixed to '0'. Reading these					
		bits will result in a '000'. Any data written					
		into these bits using the Register Write					
		command is ignored.					

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R3 - Status Register

Address 0x3

Type Read Only

Reset Default 8h'0F

Bit	Field Name	Description or Comment
7	Reserved	Reserved, read returns 0
6	Reserved	Reserved, read returns 0
5	User Bit	Unused, read returns 0
4	User Bit	Unused, read returns 0
3	Fixed OK	Unused, read returns 1
2	ю ок	Unused, read returns 1
1	Memory OK	Unused, read returns 1
0	Core OK	Unused, read returns 1

R4 - PWI Version Number Register

Address 0x4

Type Read Only

Reset Default 8h'01

Bit	Field Name	Description or Comment
7:0	Version	Read transaction will return 8h'01 indicating PWI 1.0 specification. Write
		transactions to this register are ignored.

R5 - N-Well Bias Register

Address 0x5

Type R/W

Reset Default 8h'00

Bit	Field Name	Description or Comr	Description or Comment			
7	Sign	1: Negative offset 0: Positive offset				
6:2	Voltage	Sign Data Code [7]	Voltage Data Code [6:2]	Voltage Offset from core voltage		
		0	5h'19 – 5h'1f	1 V		
			5h'01 – 5h'18	0.042 - 1 V, 0.042 V steps		
			5h'00	Active clamp to SW_AVS (default)		
		1	5h'00	0V		
			5h'01 – 5h'0f	-0.0210.315V, -0.021 V steps		
			5h'10 -5h'1f	-0.315 V		
0:1	Unused		•	•		

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R6 - P-Well Bias Register

Address 0x6

Type R/W

Bit	Field Name	Description or Commen	t	
7	Sign	1: Negative offset		
		0: Positive offset		
6:2	Voltage	Sign Data Code [7]	Voltage Data Code [6:2]	Voltage Offset from
				ground
		0	5h'10 -5h'1f	0.3 V
			5h'01 – 5h'0f	0.021 - 0.3V, 0.021 V
				steps
			5h'00	Active clamp to ground (default)
		1	5h'00	0 V
			5h'01 - 5h'18	-0.0421 V, -0.042 V
				steps
			5h'19 – 5h'1f	-1 V
0 h l eet4U.c	com Unused		•	•

R7 – VO2 Voltage Register (I/O Voltage)

Address 0x7

Type R/W

Reset Default 8h'78

Bit	Field Name	Description or Comment		
7	Sign	This bit is fixed to '0'. Reading this bit will result in a '0'. Any data written into this bit position using the Register Write command is ignored.		
6:3	Voltage	Fixed voltage value. A code of al all zero indicates minimum voltage	Il ones indicates maximum voltage while a code of ge. Default value is in bold.	
		Voltage Data Code [6:3]	Voltage Value (volts)	
		4h'0	1.5	
		4h'1	1.5	
		4h'2	1.5	
		4h'3	1.5	
		4h'4	1.6	
		4h'5	1.7	
		4h'6	1.8	
		4h'7	1.9	
		4h'8	2	
		4h'9	2.1	
		4h'A	2.2	
		4h'B	2.3	
		4h'C	2.5	
		4h'D	2.8	
		4h'E	3	
		4h'F	3.3 (default)	
2:0	Unused	These bits are fixed to '0'. Readii into these bits using the Register	ng these bits will result in a '000'. Any data written write command is ignored.	

R8 – VO1 Voltage Register (PLL/Fixed Voltage)

Address 0x8

Type R/W

-P555

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Bit	Field Name	Description or Comment		
7	Sign	This bit is fixed to '0'. Reading this bit will result in a '0'. Any data written position using the Register Write command is ignored.		
6:3	Voltage	Fixed voltage value. A code of al all zero indicates minimum voltage	l ones indicates maximum voltage while a code of ge. Default value is in bold.	
		Voltage Data Code [6:3]	Voltage Value (volts)	
		4h'0	0.7	
		4h'1	0.8	
		4h'2	0.9	
		4h'3	1	
		4h'4	1.1	
		4h'5	1.2 (default)	
		4h'6	1.3	
		4h'7	1.4	
om		4h'8	1.5	
		4h'9	1.6	
		4h'A	1.7	
		4h'B	1.8	
		4h'C	1.9	
		4h'D	2	
		4h'E	2.1	
		4h'F	2.2	
2:0	Unused	These bits are fixed to '0'. Reading into these bits using the Register	ng these bits will result in a 3b'000. Any data written	

R9-PFM/PWM Force Register

Address 0x9

Type R/W

Reset Default 8h'00

Bit	Field Name	Description or Comment	İ	
7:4	Unused	These bits are fixed to '0'. Reading these bits will result in a '000000'. Any data written into the		
		bits using the Register Wr	ite command is ignored.	
3:2	AVS PFM/		PFM Force (bit 3)	PWM Force (bit 2)
	PWM Force	Automatic Transition	0	0
		Automatic Transition	1	1
		Forced PFM Mode	1	0
		Forced PWM Mode	0	1
1:0	DVS PFM/		PFM Force (bit 1)	PWM Force (bit 0)
	PWM Force	Automatic Transition	0	0
		Automatic Transition	1	1
		Forced PFM Mode	1	0
		Forced PWM Mode	0	1

R10 - SW_DVS Voltage Register

Address 0xA

Type R/W

Bit	Field Name	Description or Comment		
7	Sign	This bit is fixed to '0'. Reading this bit will result in a '0'. Any data written into this bit position using the Register Write command is ignored.		
6:0	Voltage	DVS voltage value. Default value is in bold.		
		Voltage Data Code [6:0]	Voltage Value (V)	
		7h'00	0.6	
		7h'xx	Linear scaling	
		7h'7f	1.2 (default)	

R11 - Enable Control Register

Address 0xB

Type R/W

Reset Default 8h'3F

Bit	Field Name	Description or Comment
7:6	Unused	
5	R10 Enable (DVS Switcher)	1: DVS switching regulator is enabled
		0: DVS switching is disabled
4	R9 Enable (LDO 4)	1: LDO 4 regulator is enabled
		0: LDO 4 regulator is disabled
3	R8 Enable (LDO 1)	1: LDO 1 regulator is enabled
		0: LDO 1 regulator is disabled
2	R6 Enable (P-Well bias)	1: P-Well bias is enabled
		0: P-Well bias is clamped to ground <which ground?=""></which>
1	R5 Enable (N-Well bias)	1: N-Well bias is enabled
		0: N-Well bias tracks register R0 (AVS switcher voltage)
0	R2 Enable (Memory Retention)	1: Memory Retention regulator is enabled
		0: Memory Retention regulator is disabled

R12 – LDO4 Voltage Register

Address 0xC

Type R/W

558	Bit	Field Name	Description or Comment			
<u>ئ</u> ة	7	Sign	This bit is fixed to '0'. Reading this bit will result in a '0'. Any data written into this bit			
-			position using the Register Write	position using the Register Write command is ignored.		
	6:3	Voltage	Fixed voltage value. A code of all	ones indicates maximum voltage while a code of all		
			zero indicates minimum voltage.	Default value is in bold.		
			Voltage Data Code [6:3]	Voltage Value (volts)		
			4h'0	1.5		
			4h'1	1.5		
			4h'2	1.5		
			4h'3	1.5		
			4h'4	1.6		
			4h'5	1.7		
			4h'6	1.8		
			4h'7	1.9		
www.DataSheet41	J.com		4h'8	2		
			4h'9	2.1		
			4h'A	2.2		
			4h'B	2.3		
			4h'C	2.5		
			4h'D	2.8		
			4h'E	3		
			4h'F	3.3 (default)		
	2:0	Unused		, ,		

R13 - GPO Control

Address 0xD

Type R/W

Reset Default 8h'00

Bit	Field Name	Description or	Comment	
7:6	Unused			
5:4 P-Well Sink These bits set the		These bits set the maximum sink cur	the maximum sink current capability for the P-Well regulator	
	Current Control		bit 5	bit 4
		Nominal	0	0
		36 uA	0	1
		52 uA	1	0
		80 uA	1	1
3	GPO_3 control	Drives high to V	DD_D	
2	GPO_2 control	Drives high to V	DD_D	
1	GPO_1 control	Drives high to V	DD_D	
0	GPO_0 control	Drives high to V	DD_D	

R14 - Reserved

Address 0xE

Type R/W

Bit	Field Name	Description or Comment
7:0	Unused	Write transactions to this register are ignored. Read transactions will
		return a "No Response Frame." A no response frame contains all zeros
		(see PWI 1.0 specification) frame.

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P5551

R15 – Manufacturer Register

Type R/W

Adress 0xF

Reset Default 8h'00

Bit	Field Name	Description or Comment
7:0	Reserved	Do not write to this register

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Operation Description

DEVICE INFORMATION

The LP5551 is a PowerWise Interface (PWI) compliant power management unit (PMU) for application or baseband processors in mobile phones or other portable equipment. It operates cooperatively with processors using National Semiconductor's Advanced Power Controller (APC) to provide Adaptive or Dynamic Voltage Scaling (AVS, DVS) which drastically improves processor efficiencies compared to conventional power delivery methods. The LP5551 consists of a high efficiency switching DC/DC buck converter to supply the AVS or DVS voltage domain, three LDOs for supplying the logic, PLL, and memory, and PWI registers and logic.

OPERATION STATE DIAGRAM

The LP5551 has four operating states: Start-up, Active, Sleep and Standby.

The Start-up state is the default state after reset. All regulators are off and PWROK output is '0'. The device will power up when the external enable-input is pulled high. After the power-up sequence LP5551 enters the Active state.

In the Active state all regulators are on and PWROK-output is '1'. Immediately after Start-up the output voltages are at

their default levels. LP5551 can be turned off by supplying the Shutdown command over PWI, or by setting ENABLE and/or RESETN to '0'. The LP5551 can be switched to the Sleep state by issuing the Sleep command.

In the Sleep state the core voltage regulator is off, but the PWROK output is still '1'. The memory voltage regulator (VO3) provides the programmed memory retention voltage. LDO1 and LDO2 are on. The LP5551 can be activated from the Sleep state by giving the Wake-up command. This resumes the last programmed Active state configuration. The device can also be switched off by giving the Shutdown command, or by setting ENABLE and/or RESETN to '0'

In the Shutdown-state all output voltages are '0', and PWROK-signal is '0' as well. The LP5551 can exit the Shutdown-state if either ENABLE or RESETN is '0'. In either case the device moves to the Start-up state. See *Figure 8*.

Figure 6 shows the LP5551 state diagram. The figure assumes that supply voltage to the regulator IC is in the valid range.

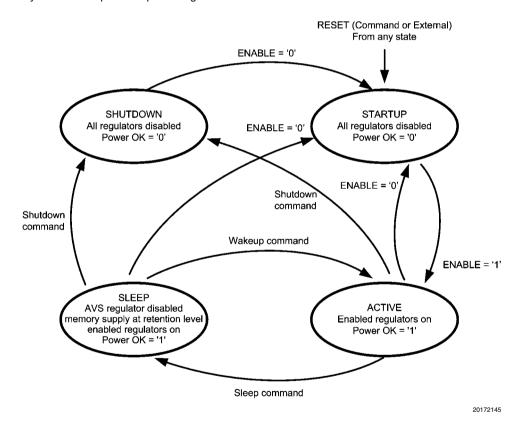


FIGURE 6. LP5551 State Diagram

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VOLTAGE SCALING

The LP5551 is designed to be used in a voltage scaling system to lower the power dissipation of baseband or application processors in mobile phones or other portable equipment. By scaling supply voltage with the clock frequency of a processor, dramatic power savings can be achieved. Two types of voltage scaling are supported, dynamic voltage scaling (DVS) and adaptive voltage scaling (AVS). DVS systems switch between pre-characterized voltages which are paired to clock frequencies used for frequency scaling in the processor. AVS systems track the processor performance and optimize the supply voltage to the required performance. AVS is a closed loop system that provides process and temperature compensation such that for any given processor, temperature, or clock frequency, the minimum supply voltage is delivered.

DIGITALLY CONTROLLED VOLTAGE SCALING

The LP5551 delivers fast, controlled voltage scaling transients with the help of a digital state machine. The state machine automatically optimizes the control loop in the LP5551 switching regulator to provide large signal transients with minimal over- and undershoot. This is an important characteristic for voltage scaling systems that rely on minimal over- and undershoot to set voltages as low as possible and save energy.

LARGE SIGNAL TRANSIENT RESPONSE

The switching converter in the LP5551 is designed to work in a voltage scaling system. This requires that the converter has a well controlled large signal transient response. Specifically, the under- and over-shoots have to be minimal or zero while maintaining settling times less than 100 usec. Typical response plots are shown in the Typical Performance section.

PowerWise™ INTERFACE

To support DVS and AVS, the LP5551 is programmable via the low power, 2 wire PowerWise Interface (PWI). This serial interface controls the various voltages and states of all the regulators in the LP5551. In particular, the switching regulator voltage can be controlled between 0.6V and 1.2V in 128 steps (linear scaling). This high resolution voltage control affords accurate temperature and process compensation in AVS. The LDO voltages can also be set, however they are not intended to be dynamic in operation. The LP5551 supports the full command set as described in PWI 1.0 specification:

- Core Voltage Adjust
- Reset
- Sleep
- Shutdown
- Wakeup
- Register Read
- Register Write
- Authenticate
- · Synchronize

PWM/PFM OPERATION

The switching converter in the LP5551 has two modes of operation: pulse width modulation (PWM) and pulse frequency

modulation (PFM). In PWM the converter switches at 1MHz. Each period can be split into two cycles. During the first cycle, the high-side switch is on and the low-side switch is off, therefore the inductor current is rising. In the second cycle, the high-side switch is off and the low-side switch is on causing the inductor current to decrease. The output ripple voltage is lowest in PWM mode *Figure 7*. As the load current decreases, the converter efficiency becomes worse due to the increased percentage of overhead current needed to operate in PWM mode. The LP5551 can operate in PFM mode to increase efficiency at low loads.

By default, the part will automatically transition into PFM mode when either of two conditions occurs for a duration of 32 or more clock cycles:

- A. The inductor valley current goes below 0 A
- B. The peak PMOS switch current drops below the I_{MODE} level:

$$I_{MODE}$$
 < 26 mA + $\frac{V_{IN}}{50\Omega}$ (typ)

During PFM operation, the converter positions the output voltage slightly higher than the nominal output voltage during PWM operation, allowing additional headroom for voltage drop during a load transient from light to heavy load. The PFM comparators sense the output voltage via the feedback pin and control the switching of the output FETs such that the output voltage ramps between 0.8% and 1.6% (typ) above the nominal PWM output voltage. If the output voltage is below the 'high' PFM comparator threshold, the PMOS power switch is turned on. It remains on until the output voltage exceeds the 'high' PFM threshold or the peak current exceeds the $I_{\rm PFM}$ level set for PFM mode. The peak current in PFM mode is:

$$I_{PFM} = 117 \text{ mA} + \frac{V_{IN}}{640} \text{ (typ)}$$

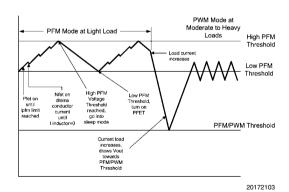


FIGURE 7. Operation in PFM Mode and Transfer to PWM Mode

Application Information

PWM/PFM FORCE REGISTER (R9)

By default, the LP5551 automatically transitions between PFM and PWM to optimize efficiency. The PWM/PFM force register (R9) provides the option to override the automatic transition and force PFM or PWM operation (see R9 – PWM/PFM Force Register declaration). Note that if the operating mode of the regulator is forced to be PFM then the switch current limit is reduced to 100 mA (50 mA average load current).

EN/RESETN

The LP5551 can be shutdown via the ENABLE or RESETN pins, or by issuing a shutdown command from PWI. To disable the LP5551 via hardware (as opposed to the PWI shutdown command), pull the ENABLE and/or the RESETN pin (s) low. To enable the LP5551, both the ENABLE and the RESETN pins must be high. Once enabled, the LP5551 engages the power-up sequence and all voltages return to their default values.

When using PWI to issue a shutdown command, the PWI will be disabled along with the regulators in the LP5551. To reenable the part, either the ENABLE, RESETN, or both pins must be toggled (high – low – high). The part will then enter the power-up sequence and all voltages will return to their default values. *Figure 8* summarizes the ENABLE/RESETN control

The ENABLE and RESETN pins provide flexibility for system control. In larger systems such as a mobile phone, it can be advantageous to enable/disable a subsystem independently. For example, the LP5551 may be powering the applications processor in a mobile phone. The system controller can power down the applications processor via the ENABLE pin, but leave on other subsystems. When the phone is turned off or in a fault condition, the system controller can have a global reset command that is connected to all the subsystems (RESETN for the LP5551). However, if this type of control is not needed, the ENABLE and RESETN pins can be tied together and used as a single enable/disable pin.

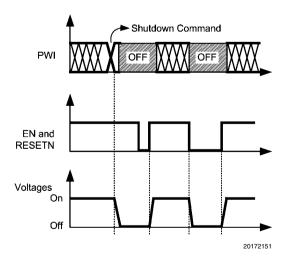


FIGURE 8. ENABLE and RESETN operation

INDUCTOR

A 4.7uH inductor should be used with the LP5551. The inductor should be rated to handle the peak load current plus the ripple current:

$$\begin{split} I_{L(MAX)} &= I_{LOAD(MAX)} + \Delta i_{L(MAX)} \\ &= I_{LOAD(MAX)} + \frac{D \times \left(V_{IN(MAX)} - V_{OUT}\right)}{2 \times L \times f_S} \\ &= I_{LOAD(MAX)} + \frac{D \times \left(V_{IN(MAX)} - V_{OUT}\right)}{9.4} \text{ (A),} \\ &\int f_S &= 1 \text{ MHz,} \\ L &= 4.7 \text{ } \mu\text{H} \end{split}$$

CURRENT LIMIT

The switching converter in the LP5551 detects the peak inductor current and limits it for protection (see Electrical Characteristics table and/or Typical Performance section). To determine the average current limit from the peak current limit, the inductor size, input and output voltage, and switching frequency must be known. The LP5551 is designed to work with a 4.7uH inductor, so:

$$\begin{split} I_{CL_AVG} &= I_{CL_PK} - \Delta i_L \\ &= I_{CL_PK} - \frac{D \times (V_{IN} - V_{OUT})}{2 \times L \times f_S} \\ &\approx 0.4 - \frac{D \times (V_{IN} - V_{OUT})}{9.4}, \left\{ \begin{array}{l} f_S = 1 \text{ MHz,} \\ L = 4.7 \text{ } \mu\text{H} \end{array} \right. \end{split}$$

INPUT CAPACITOR

The input capacitor to the switching converter supplies the AC switching current drawn from the switching action of the internal power FETs. The input current of a buck converter is discontinuous, so the ripple current supplied by the input capacitor is large. The input capacitor must be rated to handle this current:

$$I_{RMS_CIN} = I_{OUT} \frac{\sqrt{V_{OUT} \times (V_{IN} - V_{OUT})}}{V_{IN}} (A)$$

The power dissipated in the input capacitor is given by:

$$P_{D_CIN} = I_{RMS_CIN}^2 \times R_{ESR_CIN}(W)$$

The input capacitor must be rated to handle both the RMS current and the dissipated power. A 22 μF ceramic capacitor is recommended for the LP5551.

OUTPUT CAPACITOR

The switching converters in the LP5551 are designed to be used with a 22uF ceramic output capacitor. The dielectric should be X5R, X7R, or comparable material to maintain proper tolerances. The output capacitor of the switching converter absorbs the AC ripple current from the inductor and provides the initial response to a load transient. The ripple voltage at the output of the converter is the product of the ripple current flowing through the output capacitor and the impedance of the capacitor. The impedance of the capacitor can be dominated by capacitive, resistive, or inductive elements within the capacitor, depending on the frequency of the

ripple current. Ceramic capacitors are predominately used in portable systems and have very low ESR and remain capacitive up to high frequencies.

The switcher peak - to - peak output voltage ripple in steady state can be calculated as:

$$V_{PP} = I_{LPP} (R_{ESR} + \frac{1}{F_S \times 8 \times C_{OUT}})$$

LDO INFORMATION

The LDOs included in the LP5551 provide static supply voltages for various functions in the processor. Use the following sections to determine loading and external components.

LDO LOADING CAPABILITY

The LDOs in the LP5551 can regulate to a variety of output voltages, depending on the need of the processor. These voltages can be programmed through the PWI. Table 1 summarizes the parameters of the LP5551 LDOs.

TABLE 1. LDO Parameters

		PWI Register	Output voltage range	Recommended Maximum	Dropout Voltage	Typical Load
J.O	om			Output Current	(typical)	
	LDO1	R8	0.6 V – 2.2 V	100 mA	200 mV	PLL
	LDO2	R7	1.5 V – 3.3 V	250 mA	150 mV	I/O
	LDO3	R2	V _{OSW} + 0.05 V ¹	50 mA	200 mV	Memory/Memory
			0.7 V - 1.35 V ²			retention
	LDO4	R12	1.5 V – 3.3 V	250 mA	150 mV	User defined

1. LDO3 tracks the switching converter output voltage (V_{OSW}) plus a 50 mV offset when the LP5551 is in active state.

2. LDO3 regulates at the set memory retention voltage when the LP5551 is in shutdown state.

LDO OUTPUT CAPACITOR

The output capacitor sets a low frequency pole and a high frequency zero in the control loop of an LDO. The capacitance and the equivalent series resistance (ESR) of the capacitor must be within a specified range to meet stability require-

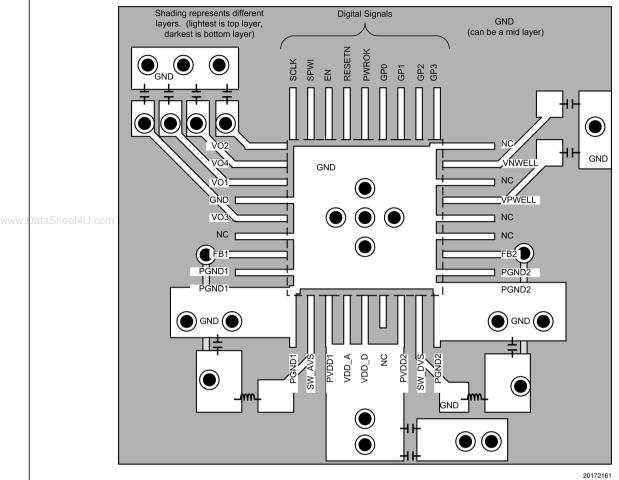
ments. The LDOs in the LP5551 are designed to be used with ceramic output capacitors. The dielectric should be X5R, X7R, or comparable material to maintain proper tolerances. Use the following table to choose a suitable output capacitor:

TABLE 2. Output Capacitor Selection Guide

	Output Capacitance Range (Recommended Typical Value)	ESR range
LDO1	1 μ F – 20 μ F (2.2 μ F)	5 mohm – 500 mohm
LDO2	$2 \mu F - 20 \mu F (4.7 \mu F)$	5 mohm – 500 mohm
LDO3	$0.7 \mu F - 2.2 \mu F (1.0 \mu F)$	5 mohm- 500 mohm
LDO4	$2 \mu F - 20 \mu F (4.7 \mu F)$	5 mohm – 500 mohm

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BOARD LAYOUT CONSIDERATIONS



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FIGURE 9. Board Layout Design Recommendations for the LP5551

Notes	LP5551
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Notes

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